Foreword

The science and technology of wide-bandgap semiconductor materials continue to advance and pervade an increasing number of device applications. For 15 consecutive years, the Journal of Electronic Materials has published a special issue on wide-bandgap semiconductors. Initially focused on SiC and the group III nitride semiconductors, the special issue was expanded in 2004 to include ZnO and related II–VI oxide semiconductors. All of these wide-bandgap semiconductor materials continue to be the focus of worldwide research and development activity.

This special issue includes papers on materials growth, characterization, processing, nanostructures, and devices based on wide-bandgap semiconductors. Many of the papers were also presented at the 50th Electronic Materials Conference (EMC), held in June 2008 at the University of California, Santa Barbara. The conference remains a lively annual forum for the discussion of research on wide-bandgap semiconductors.

Publication of this special issue was made possible only through the efforts of many authors, reviewers, editors, and journal staff members, and we thank them all for their invaluable contributions.

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